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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.	APPLICATION NO.
03680036AA	not assigned
APPLICANT(S)	10575785 - GAU: 2813
K. Takahashi, et al.	
FILING DATE	GROUP ART UNIT
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
/S.W.S./	BA	2003-258121	9/2003	Japan				✓
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/S.W.S./	CA	Lee, JH, et al., "Tunable Work Function Dual Metal Gate Technology for Bulk and Non-Bulk CMOS", IEEE (2002)
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ATTY DOCKET NO.	APPLICATION NO.
03680036AA	10/575,785
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K. Takahashi, et al.	10575785 - GAU: 2813
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/S.W.S./	CC	Kedzierski, J., et al., "Threshold voltage control in NiSi-gated MOSFETs through silicidation induced impurity segregation (SIIS)", IEEE (2003)
/S.W.S./	CD	Maszara, W.P., et al., "Transistors with Dual Work Function Gates by Single Full Silicidation (FUSI) of Polysilicon Gates", IEEE (2002), pp. 367–370

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